

Features

- Frequency: 6GHz~18GHz
- Power Gain: 17dB
- Psat: 40dBm
- P.A.E.:20%
- +24V@1A(Quiescent)
- Chip Size: 4.5mm×3.4mm×0.1mm

Electrical Specification (TA=+25°C, Vd=+24V, Vg=-2.2V)

Parameter	Min.	Typ.	Max.	Unit
Frequency	6-18			GHz
Psat	40	40.5		dBm
P.A.E.	20	25		%
Power Gain	16	17		dB
VSWRin		2.5		-
Operating Current		2		A

Note: 1) All chips have been on-chip 100% DC and RF tested .
2)RF Test Condition: Vd=+24V, Vg=-2.2V, CW.

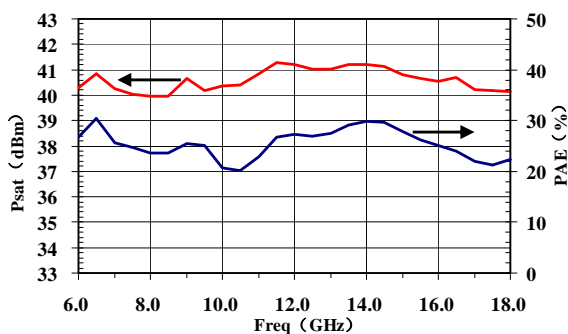
More Temperature Testing Results can be provided upon Requested.

Limited Rating Values

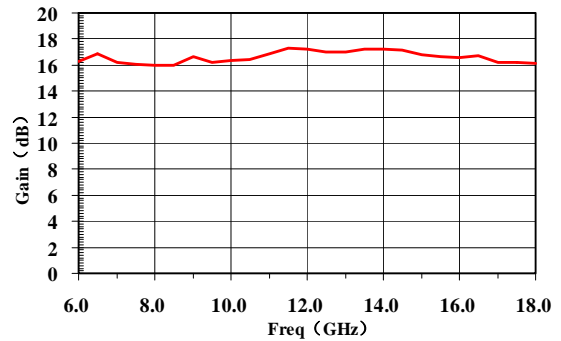
Max Input Vd	+28V
Max Input Power	+30dBm
Storage Temperature	-65°C ~ +150°C
Operating Temperature	-55°C ~ +125°C

Typical Testing Curves

Output Psat/Efficiency VS Frequency

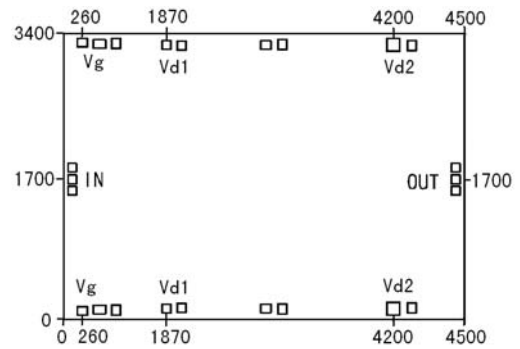


Power Gain VS Frequency



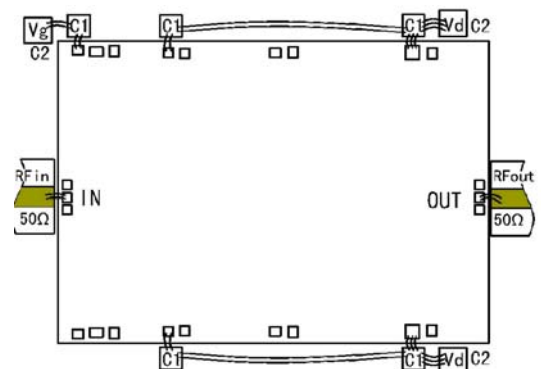
Dimensions and Outline

NC11609C-618P10 outline



Note: The unit is um. Dimension of In/Out Pad 100×100µm².

Assembly Diagram



Note: External capacitor c1=100pF,c2=0.01µF.
Diameter of bonding golden wire: 25µm.
Pay attention to heat dissipation when used in CW.

Attention

- 1) 2 bonding wires should be used for Input/Output. The length of the wires should be shorter than 350µm.
- 2) Bonding with 80/20 Au/Sn. The bonding temperature should be lower than 300°C and the time should be less than 30 seconds.
- 3) Antistatic protection should be taken.